Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSV)

2SK2843

Chopper Regulator, DC-DC Converter and Motor Drive Applications

• Low drain—source ON resistance : RDS (ON) = 0.54Ω (typ.) • High forward transfer admittance : $|Y_{fs}| = 9.0 S$ (typ.) • Low leakage current : IDSS = $100 \mu A$ (max) (VDS = 600 V) • Enhancement mode : $V_{th} = 2.0 \sim 4.0 V$ (VDS = 10 V, ID = 1 mA)

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	600	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	600	V	
Gate-source voltage		V_{GSS}	±30	V	
Drain current	DC (Note 1)	I_{D}	10	Α	
	Pulse (Note 1)	I_{DP}	40	Α	
Drain power dissipatio	n (Tc = 25°C)	P_{D}	45	W	
Single pulse avalanche energy (Note 2)		E _{AS}	363	mJ	
Avalanche current		I _{AR}	10	Α	
Repetitive avalanche energy (Note 3)		E _{AR}	5.0	mJ	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

2-10R1B

Weight: 1.9 g (typ.)

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Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	2.78	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	62.5	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 6.36 mH, R_{G} = 25 Ω , I_{AR} = 10 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic-sensitive device.

Please handle with caution.



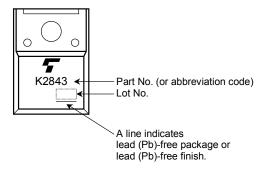
Electrical Characteristics (Ta = 25°C)

Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±25 V, V _{DS} = 0 V	_	_	±10	μΑ
Gate-source bro	eakdown voltage	V (BR) GSS	I _G = ±10 μA, V _{DS} = 0 V	±30	_	_	V
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	_	_	100	μΑ
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	600	_	_	V
Gate threshold v	/oltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	2.0	_	4.0	V
Drain-source O	N resistance	R _{DS (ON)}	V _{GS} = 10 V, I _D = 5 A	_	0.54	0.75	Ω
Forward transfe	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 5 A	3.0	9.0	_	S
Input capacitano	ce	C _{iss}			2040	_	pF
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	230	_	
Output capacitance		C _{oss}		_	590	_	
Switching time	Rise time	t _r	V_{GS} V_{OUT} V_{OUT} V_{OUT} V_{OUT} V_{OUT}	_	22	_	
	Turn-on time	t _{on}		_	58	_	nc
	Fall time	t _f		_	36	_	ns
	Turn-off time	t _{off}	$V_{DD} = 200V$ Duty $\leq 1\%$, $t_{\mathbf{w}} = 10 \mu \text{s}$	_	190	_	
Total gate charge (gate-source plus gate-drain)		Qg	V _{DD} ≈ 400 V, V _{GS} = 10 V, I _D = 10 A		45	-	
Gate-source charge		Q _{gs}		_	25		nC
Gate-drain ("miller") Charge		Q _{gd}		_	20		

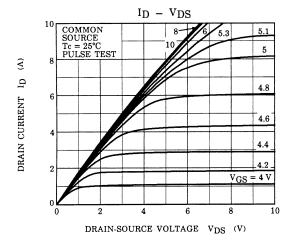
Source-Drain Ratings and Characteristics (Ta = 25°C)

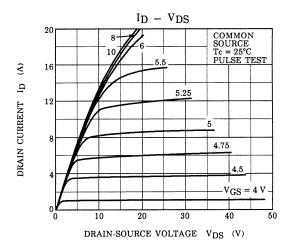
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	10	Α
Pulse drain reverse current (Note 1)	I _{DRP}	-	_	_	40	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = 10 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 10 A, V _{GS} = 0 V	1	1300		ns
Reverse recovery charge	Q _{rr}	dl _{DR} / dt = 100 A / μs	_	16	_	μC

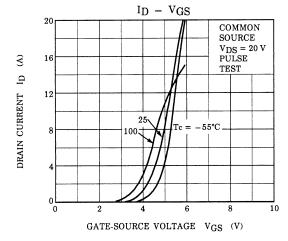
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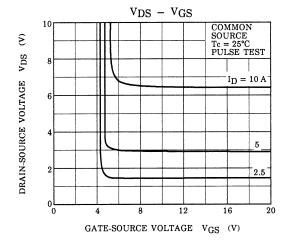


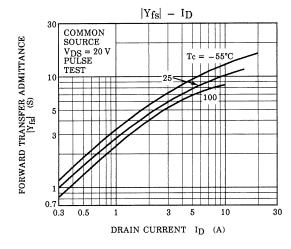
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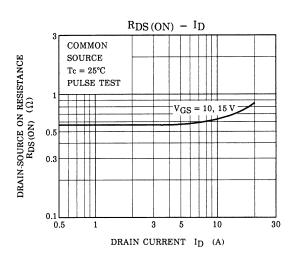


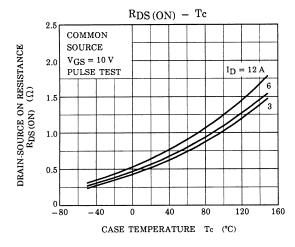


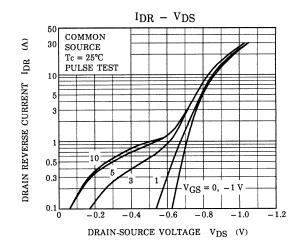


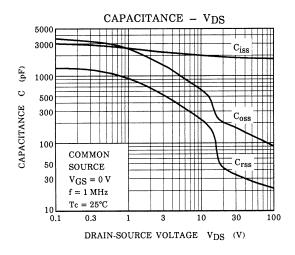


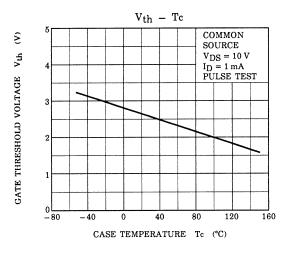


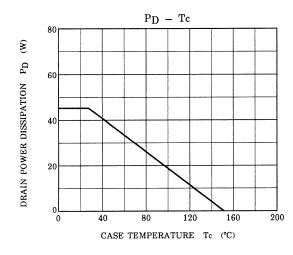


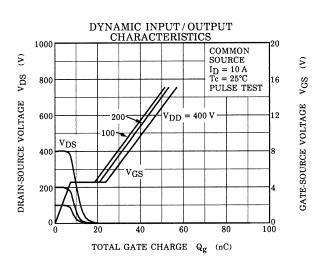




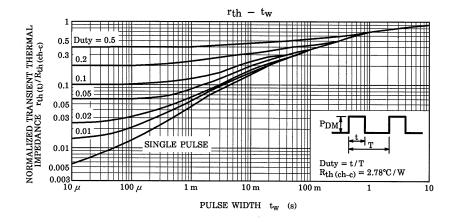


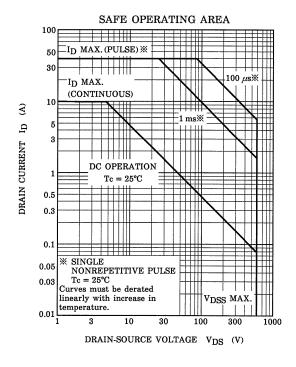


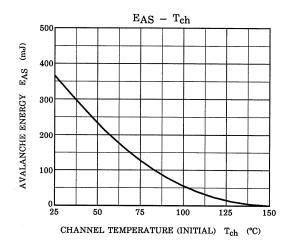


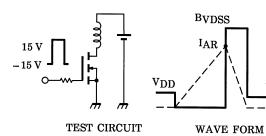


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$$R_G = 25 \Omega$$

 $V_{DD} = 90 \text{ V}, L = 6.36 \text{ mH}$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^{2} \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

 v_{DS}

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Handbook" etc..

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